

2SC495

2SC496

SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07407 0 T-29-23

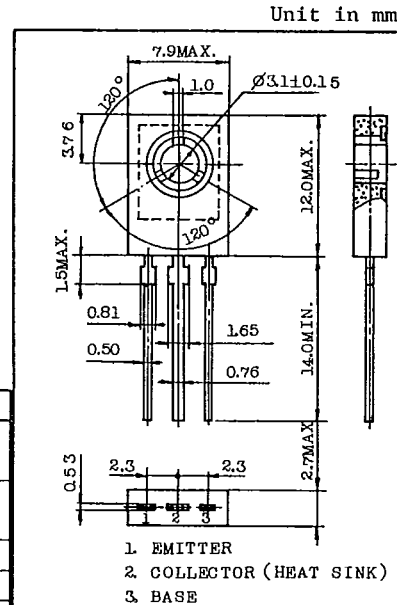
MEDIUM POWER AMPLIFIER APPLICATIONS.

FEATURES:

- Low Collector Saturation Voltage
: $V_{CE(sat)}=0.25V$ (Typ.)
- 0.5 ~ 2 Watts Output Application.
- Complementary to 2SA505 and 2SA496.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	2SC495	70
		2SC496	40
Collector-Emitter Voltage	V _{CEO}	2SC495	50
		2SC496	30
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	1	A
Emitter Current	I _E	-1	A
Collector Power Dissipation	P _C	1	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55 ~ 150	°C



JEDEC TO - 126

EIAJ -

TOSHIBA 2 - 8F1A

Mounting Kit No. AC46C

Weight : 0.72g

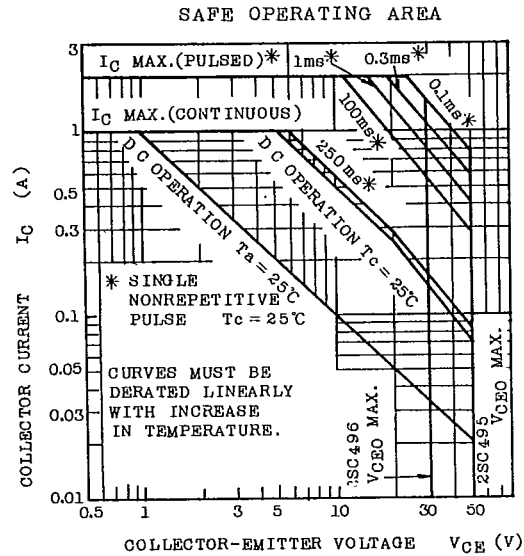
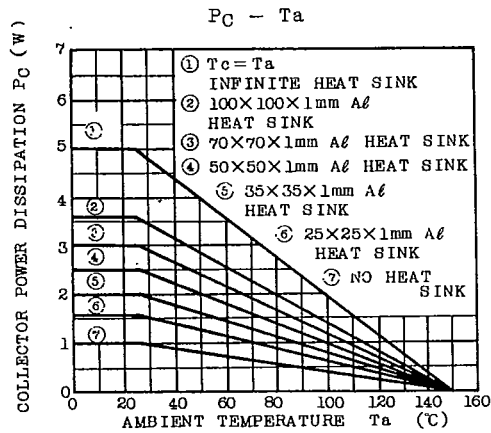
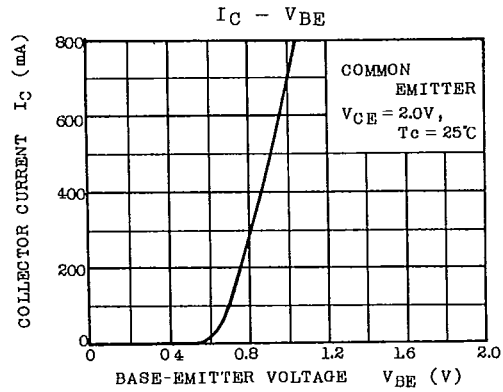
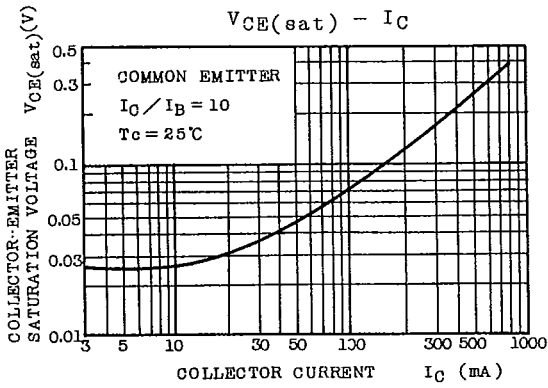
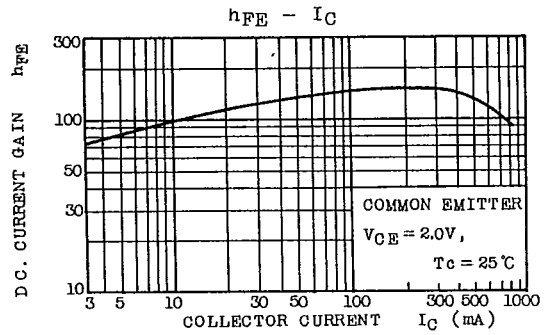
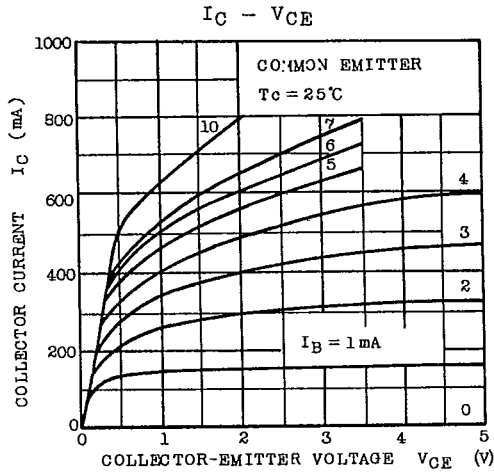
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector Cut-off Current	I _{CB0}	V _{CB} =30V, I _E =0	-	-	1.0	μA	
Emitter Cut-off Current	I _{EBO}	V _{EB} =5V, I _C =0	-	-	1.0	μA	
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	I _C =10mA, I _B =0	2SC495	50	-	-	V
			2SC496	30	-	-	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	I _E =1mA, I _C =0	5	-	-	V	
DC Current Gain	h _{FE(1)} (Note)	V _{CE} =2V, I _C =50mA	40	-	240		
	h _{FE(2)}	V _{CE} =2V, I _C =800mA	13	-	-		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C =500mA, I _B =50mA	-	0.25	0.8	V	
Base-Emitter Voltage	V _{BE}	V _{CE} =2V, I _C =500mA	-	0.9	1.1	V	
Transition Frequency	f _T	V _{CE} =10V, I _C =10mA	50	100	-	MHz	
Collector Output Capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1MHz	-	10	-	pF	

Note : h_{FE(1)} Classification R : 40~80, O : 70~140, Y : 120~240

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